

物理学会 22aGQ-11

富山大 11/9/22

P, Bを含んだSi結晶の積層欠陥エネルギーの
第一原理計算

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東北大金研 大野裕, 徳本有紀, 米永一郎

First principles calculations of stacking fault
energies of P and B doped Si crystals.

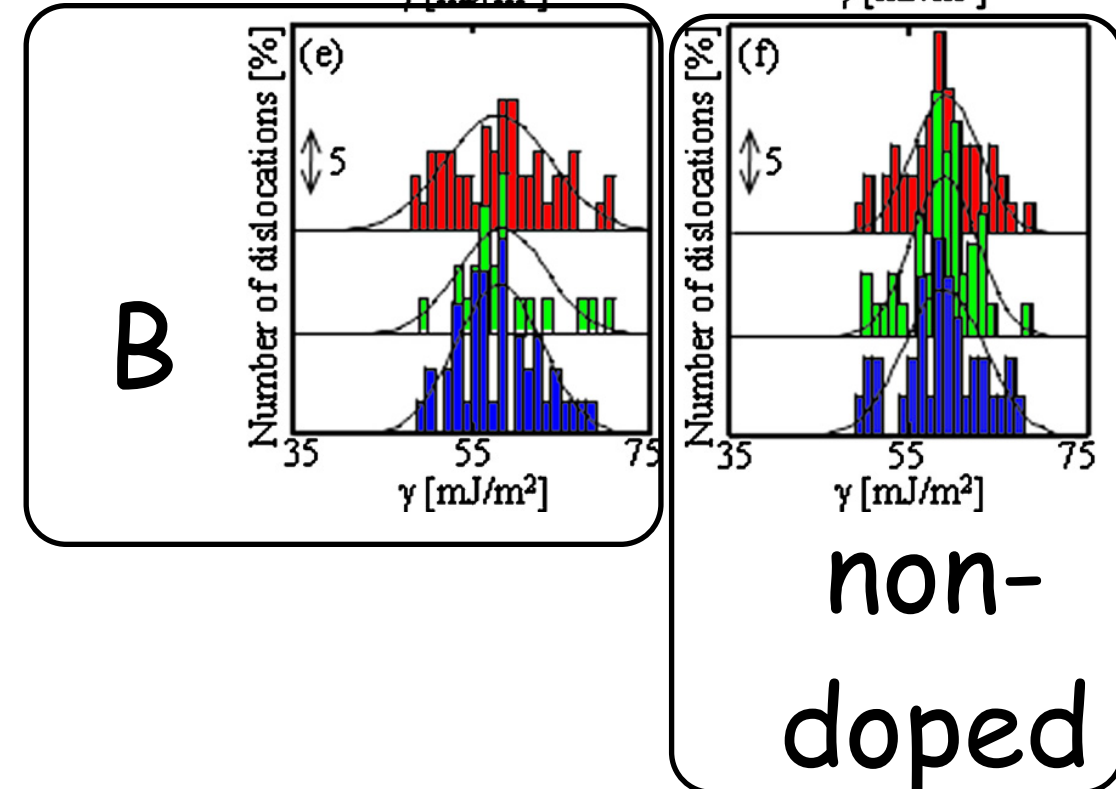
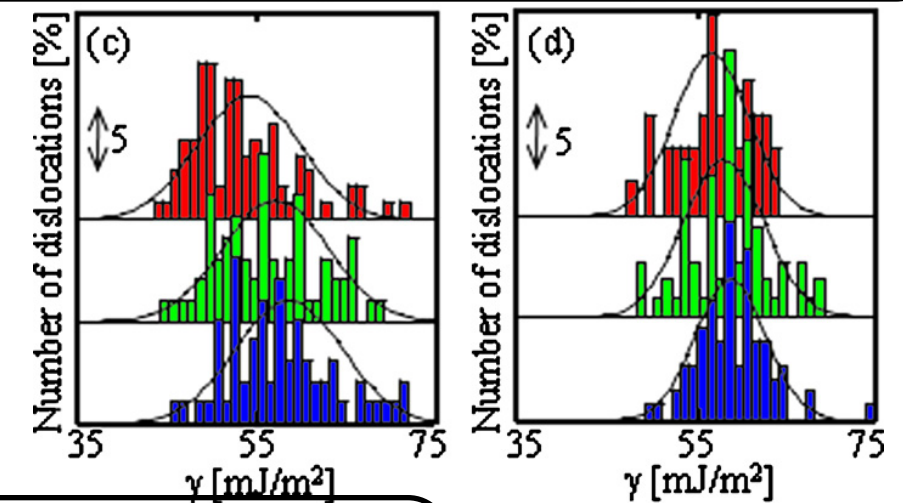
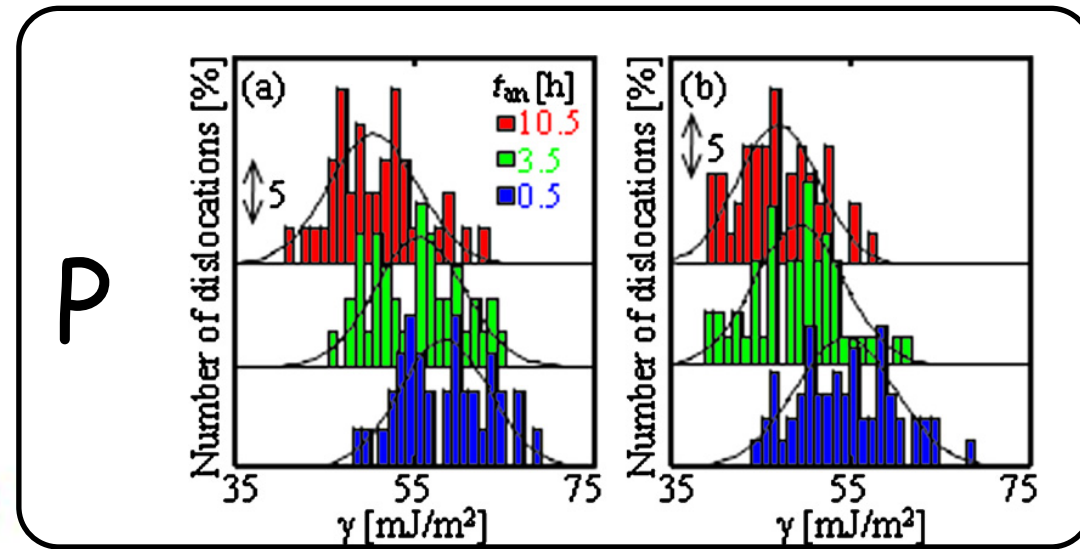
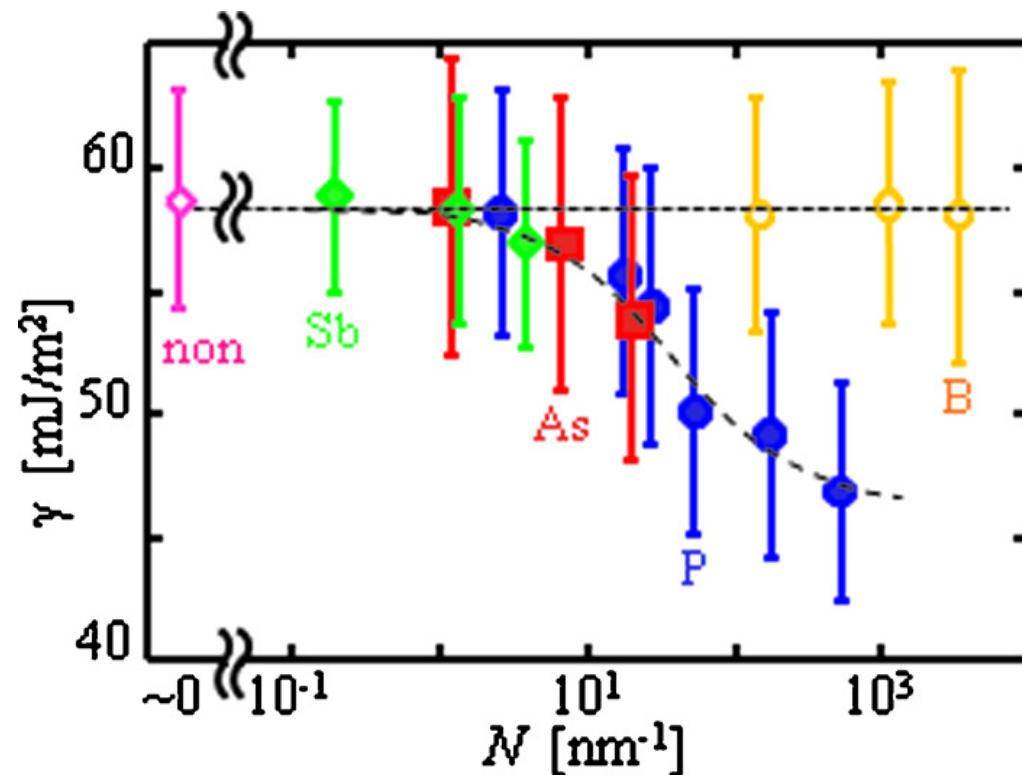
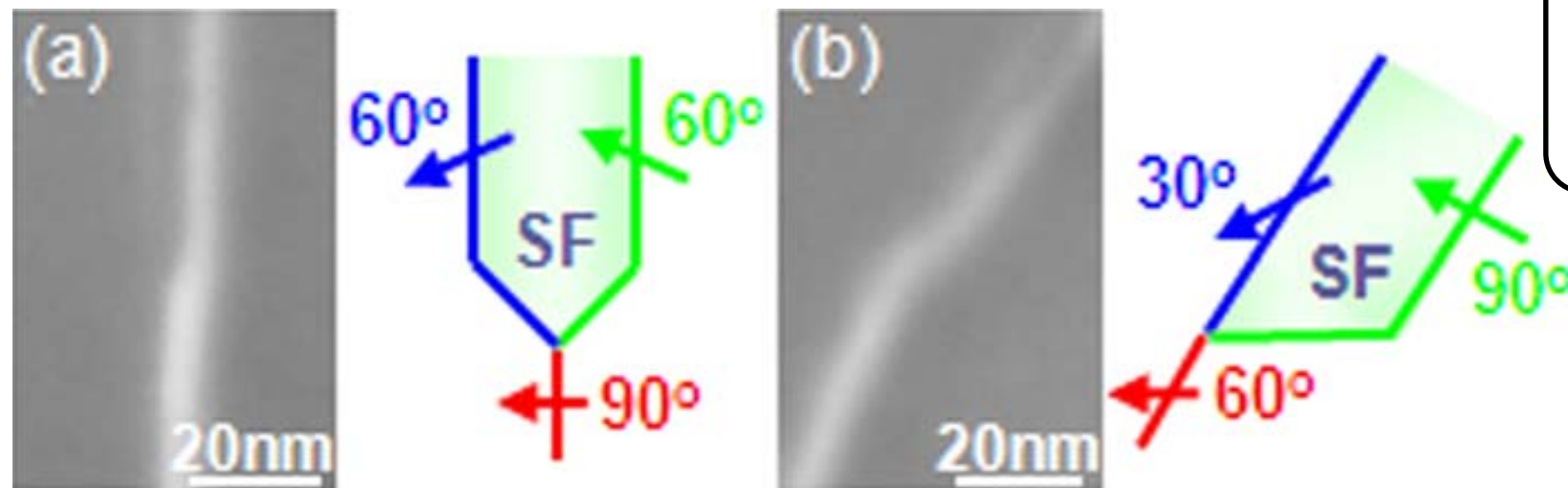
Kwansei Gakuin Univ.,

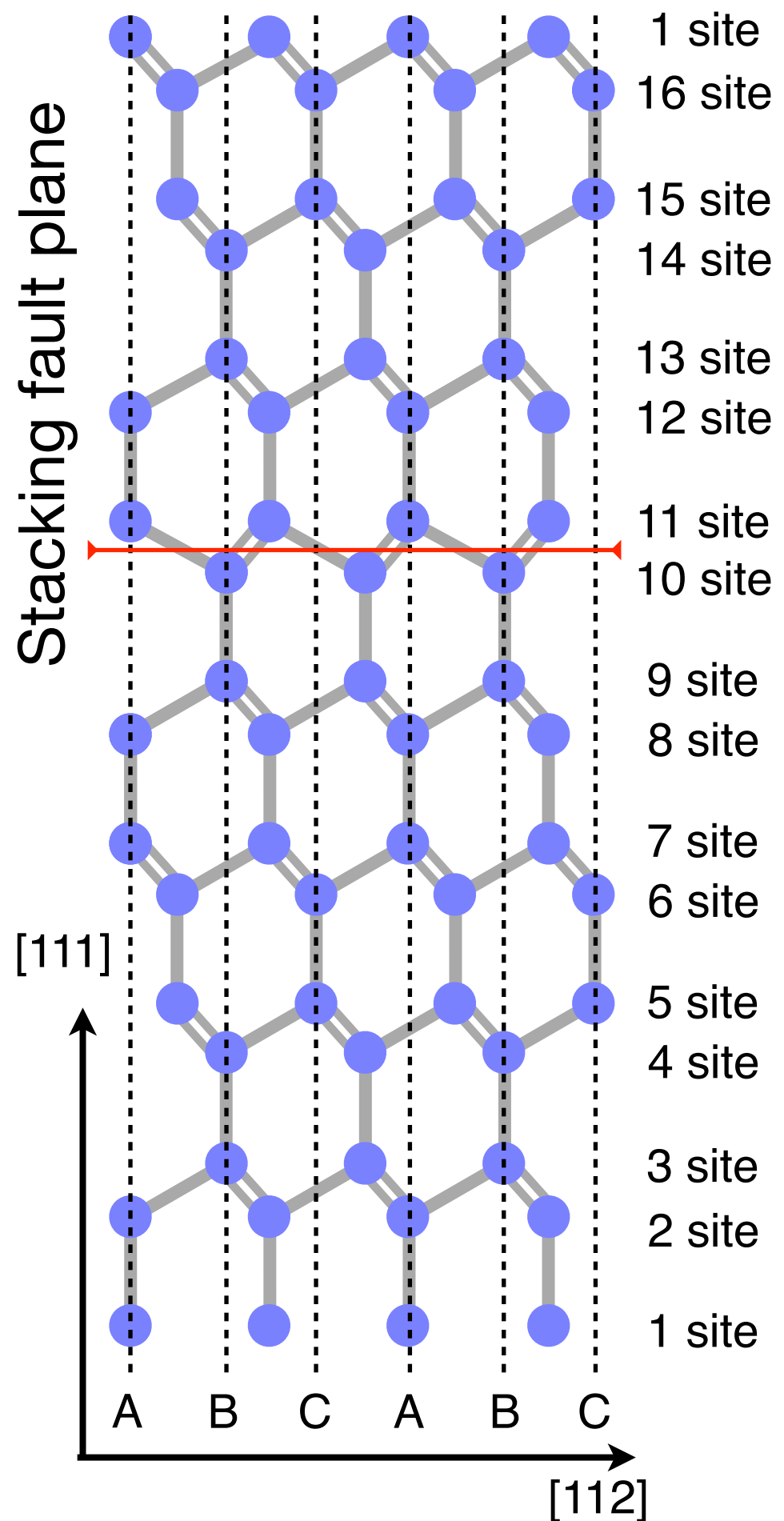
Shigeto R. Nishitani, Kensuke Togase,

Tohoku Univ.,

Yutaka Ohno, Yuki Tokumoto, Ichiro Yonenaga.

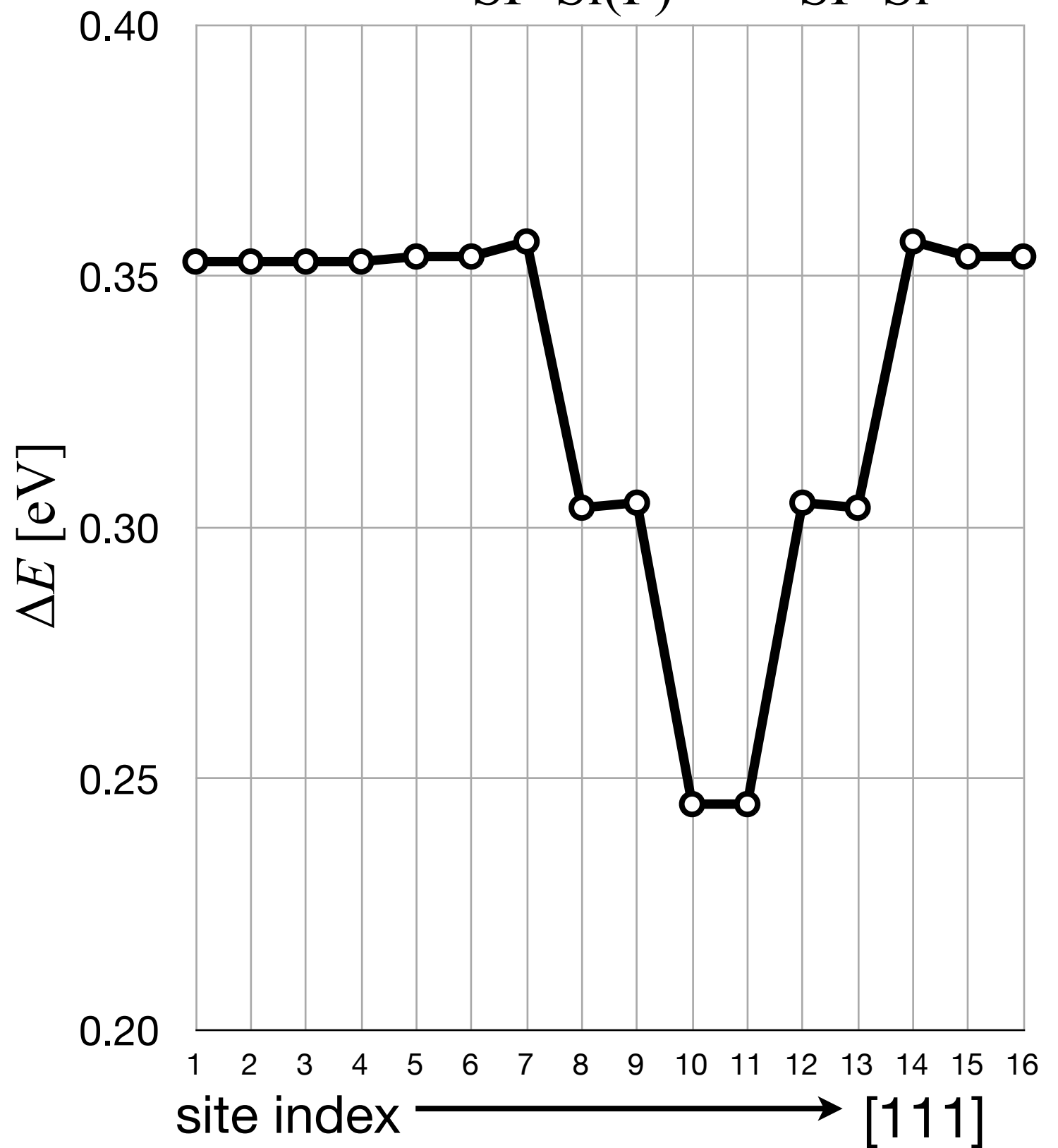
Ohno's results





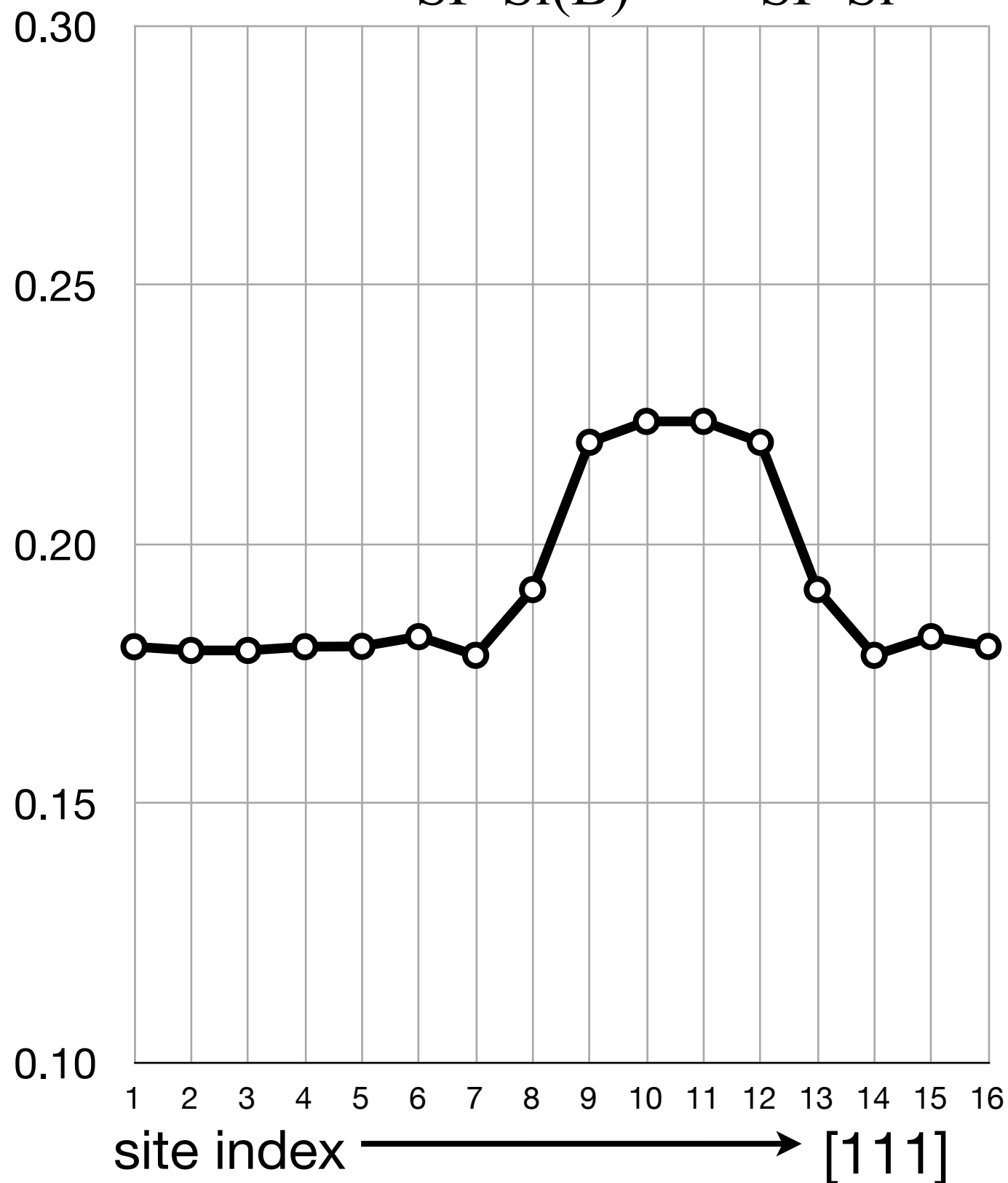
Si+P

$$\Delta E = E_{\text{SF-Si(P)}} - E_{\text{SF-Si}}$$



Si+B

$$\Delta E = E_{\text{SF-Si(B)}} - E_{\text{SF-Si}}$$



Result

[0001]

